

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Frank Cardone, et al.

Examiner: Unassigned

Serial No.: To be assigned

Art Unit: Unassigned

Filed: Herewith

Docket: YOR919970121US2 (16323A)

For: ABRUPT "DELTA-LIKE" DOPING
IN Si AND SiGe FILMS BY UHV-CVD

Dated: December 12, 2003

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.97 and 1.98, it is requested that the following references, which are also listed on the attached Form PTO-1449, be made of record in the above-identified case.

1. U.S. Patent No. 5,316,958, dated May 31, 1994;
2. U.S. Patent No. 5,628,834, dated May 13, 1997;
3. U.S. Patent No. 5,047,365, dated September 10, 1991;

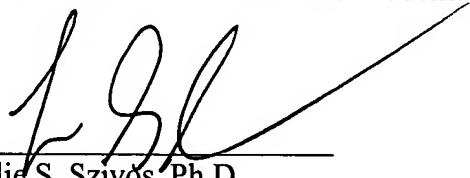
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Dated: December 12, 2003



Leslie S. Szivos, Ph.D.

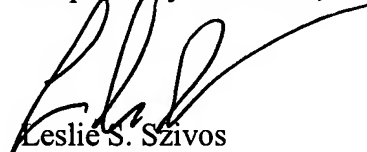
4. U.S. Patent No. 5,241,197, dated August 31, 1993;
5. U.S. Patent No. 5,298,452, dated March 29, 1994;
6. U.S. Patent No. 5,089,428, dated February 18, 1992;
7. U.S. Patent No. 5,616,515, dated April 1, 1997;
8. U.S. Patent No. 5,607,511, dated March 4, 1997;
9. U.S. Patent No. 5,181,964, dated January 20, 1993;
10. European Patent Publication No. 494,395, dated July 15, 1992;
11. Japanese Patent Publication No. 2-288328, dated November 28, 1988;
12. Japanese Patent Publication No. 63-168021, dated July 12, 1988;
13. Japanese Patent Publication No. 6,061,489, dated March 4, 1994;
14. Sheldon P. et al. (1986) "Growth, Nucleation, and Electrical properties of Molecular Beam Epitaxially grown, As-doped Ge on Si Substrates" J. Vac. Sci & Tech. A, Vol. 4, No. 3, pt. 1, pgs. 889-893;
15. Ismail K, et al (1992) "High Transconductance n-type Si/SiGe Modulation-Doped Field-Effect Transistors" IEEE Electron Device Letters, Vol. 13, No. 5, pgs. 229-231; and
16. Ismail K, et al. (1991) High Electron Mobility in Modulation-Doped Si/SiGe" Applied Physics Letters, Vol. 58, No. 19, pgs. 2117-2119.

Pursuant to 37 C.F.R. §1.98 (d), copies of the references listed on the enclosed Form PTO-1449 are not provided since they were previously made record of in the parent application Serial No. 09/810,856 filed on March 16, 2001. Reference No. 1 was cited in the Information Disclosure Statement filed on September 16, 1998 and references 2-7 were cited by the Patent and Trademark Office in an Office Action dated on November 10, 1998, references 8 and 9 were cited by the Patent and Trademark Office in an Office Action dated January 26, 2001 and references 10-16 were cited by the Patent and Trademark Office in an Office Action dated August 24, 2001. Consideration of this Information Disclosure Statement is respectfully requested, since the information provided herewith may be material to the

examination of the present application as defined under 37 C.F.R. § 1.56. This statement is not intended to represent that a search has been performed or that no other art than that identified herein exists.

The instant Information Disclosure Statement is being submitted concurrent with the filing of the present application. Therefore, this filing is made under 37 C.F.R. § 1.97(b)(1). An Information Disclosure Statement filed under 37 C.F.R. § 1.97(b)(1) requires neither certification nor fee.

Respectfully submitted,



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LSS/sf
Enclosure PTO 1449

Form PTO-1449 • U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE				Atty. Docket No. YOR919970121US2 (16323A)		Serial N . To be assigned	
LIST OF PRIOR ART CITED BY APPLICANT (Use several sheets if necessary)				Applicant Frank Cardone, et al.			
				Filing Date Herewith		Group Unassigned	

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL*		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
	AA	5,316,958	5/31/1994	Meyerson			
	AB	5,628,834	5/13/1997	Copel et al.			
		5,047,365	9/10/1991	Kawanaka et al.			
		5,241,197	8/31/1993	Murakami et al.			
		5,298,452	3/29/1994	Meyerson			
		5,089,428	2/18/1992	Verret et al.			
		5,616,515	4/1/1997	Okuno			
		5,607,511	3/4/1997	Meyerson			
		5,181,964	1/20/1993	Meyerson			
		5,227,644	7/1993	Ueno			

FOREIGN PATENT DOCUMENTS								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
		494,395	7/15/1992	Europe				
		2-288328	11/28/1998	Japan				
		63-168021	7/12/1988	Japan				
		6,061,489	3/4/1994	Japan				

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
	Sheldon P. et al. (1986) "Growth, Nucleation, and Electrical properties of Molecular Beam Epitaxially grown, As-doped Ge on Si Substrates" J. Vac. Sci & Tech. A, Vol. 4, No. 3, pt. 1, pgs. 889-893;
	Ismail K, et al (1992) "High Transconductance n-type Si/SiGe Modulation-Doped Field-Effect Transistors" IEEE Electron Device Letters, Vol. 13, No. 5, pgs. 229-231; and
	Ismail K, et al. (1991) High Electron Mobility in Modulation-Doped Si/SiGe" Applied Physics Letters, Vol. 58, No. 19, pgs. 2117-2119.

EXAMINER	DATE CONSIDERED
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.